

**IN THE SPECIFICATION:**

**Please rewrite** the paragraph at page 3, lines 5-16, so that it reads as follows:

To that end, the invention provides a method of measuring defocusing, comprising the steps of applying a resist to the top surface of a semiconductor wafer, subjecting the resist to exposure to light by deviating a focus of the light by a given distance away from the resist, using a pattern exposure system, and by using a mask patterned in a geometrical figure comprising a plurality of small rectangles, each narrower in width than a resolution limit of the pattern exposure system, provided on four sides of a large rectangle, and arranged so as to be perpendicular longitudinally or parallel transversely to the respective ~~fourides~~ four sides of the large rectangle, forming a resist pattern by developing the resist after the step of subjecting the resist to the exposure to light, and finding defocusing in relation to the resist on the basis of a length of the resist pattern.